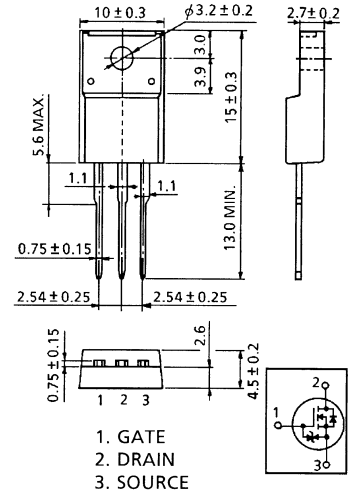
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIII)

2SK3754

Relay Drive, DC−DC Converter and
Motor Drive Applications

- 4.5-V gate drive
- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 71 mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 5.0 S (typ.)
- Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 30 V)
- Enhancement-model: V_{th} = 1.3~2.5 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



JEDEC	—
JEITA	SC-67
TOSHIBA	2-10R1B

Weight: 1.9 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	5	A
	Pulse (Note 1)	I_{DP}	15	
Drain power dissipation (Tc = 25°C)		P_D	25	W
Single pulse avalanche energy (Note 2)		E_{AS}	4.0	mJ
Avalanche current		I_{AR}	2.5	A
Repetitive avalanche energy (Note 3)		E_{AR}	2.5	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th\ (ch-c)}$	5.0	°C/W
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	62.5	°C/W

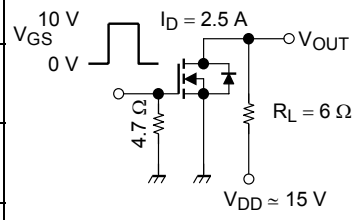
Note 1: Please use devices on conditions that the channel temperature is below 150°C.

Note 2: V_{DD} =24 V, T_{ch} = 25°C (initial), L = 0.5 mH, R_G = 25 Ω, I_{AR} = 2.5 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

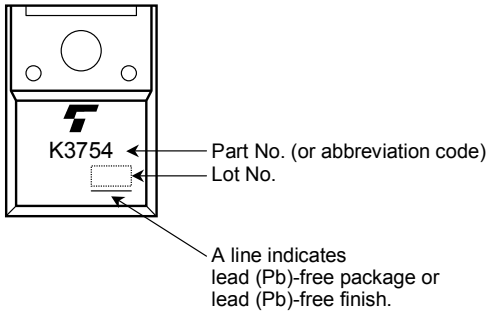
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut-off current		I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	30	—	—	V
		$V_{(BR)\ DSX}$	I_D = 10 mA, V_{GS} = −20 V	15	—	—	
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	1.3	—	2.5	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 4.5 V, I_D = 2.5 A	—	78	99	mΩ
			V_{GS} = 10 V, I_D = 2.5 A	—	71	89	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 2.5 A	2.5	5.0	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	1250	—	pF
Reverse transfer capacitance		C_{rss}		—	155	—	
Output capacitance		C_{oss}		—	170	—	
Switching time	Rise time	t_r		—	7	—	ns
	Turn-on time	t_{on}		—	16	—	
	Fall time	t_f		—	18	—	
	Turn-off time	t_{off}	Duty ≦ 1%, t_w = 10 μs	—	69	—	
Total gate charge		Q_g	V_{DD} ≃ 24 V, V_{GS} = 10 V, I_D = 5 A	—	25	—	nC
Gate-source charge		Q_{gs}		—	20	—	
Gate-drain charge		Q_{gd}		—	5	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	15	A
Reverse recovery time	t_{rr}	I_{DR} = 5 A, V_{GS} = 0 V,	—	37	—	ns
Reverse recovery charge	Q_{rr}	dI_{DR}/dt = 50 A/μs	—	20	—	nC

Marking



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